PD - 96334

AUIRGS30B60K

 $V_{CES} = 600V$ 

AUIRGSL30B60K

# International

### AUTOMOTIVE GRADE

### INSULATED GATE BIPOLAR TRANSISTOR

### Features

- Low  $V_{CE(on)}$  Non Punch Through IGBT Technology
- 10µs Short Circuit Capability
- Square RBSOA
- Positive V<sub>CE(on)</sub> Temperature Coefficient
- Maximum Junction Temperature rated at 175°C
- Lead-Free, RoHS Compliant
- Automotive Qualified \*

### **Benefits**

- Benchmark Efficiency for Motor Control
- Rugged Transient Performance
- Low EMI
- Excellent Current Sharing in Parallel Operation

# $G = \frac{1}{E}$ **n-channel** $I_{C} = 50A, T_{C} = 100^{\circ}C$ $at T_{J} = 175^{\circ}C$ $t_{sc} > 10\mu s, T_{J} = 150^{\circ}C$ $V_{CE(on)} typ. = 1.95V$

С

D<sup>2</sup>Pak TO-262 AUIRGS30B60K AUIRGSL30B60K

G	С	E
Gate	Collector	Emitter

### **Absolute Maximum Ratings**

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ( $T_A$ ) is 25°C, unless otherwise specified

	Parameter	Max.	Units
V <sub>CES</sub>	Collector-to-Emitter Voltage	600	V
I <sub>C</sub> @ T <sub>C</sub> = 25°C	Continuous Collector Current	78	
I <sub>C</sub> @ T <sub>C</sub> = 100°C	Continuous Collector Current	50	А
I <sub>CM</sub>	Pulse Collector Current (Ref.Fig.C.T.5)	120	
I <sub>LM</sub>	Clamped Inductive Load current ${}^{}$	120	
VISOL	RMS Isolation Voltage, Terminal to Case, t=1 min.	2500	V
V <sub>GE</sub>	Gate-to-Emitter Voltage	±20	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	370	W
P <sub>D</sub> @ T <sub>C</sub> = 100°C	Maximum Power Dissipation	180	
TJ	Operating Junction and	-55 to +175	
T <sub>STG</sub>	Storage Temperature Range		°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

### **Thermal / Mechanical Characteristics**

	Parameter	Min.	Тур.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case- IGBT			0.41*	
R <sub>0CS</sub>	Case-to-Sink, flat, greased surface		0.50		°C/W
R <sub>0JA</sub>	Junction-to-Ambient (PCB Mount, Steady State)			40	
Wt	Weight		1.44	_	g

\*  $R_{\theta JC}$  (end of life) = 0.65°C/W. This is the maximum measured value after 1000 temperature cycles from -55 to 150°C and is accounted for by the physical wearout of the die attach medium.

Dynamic Electrical Characteristics @	$T_{\rm J} = 25^{\circ}C$ (unless)	otherwise specified)
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	Parameter	Min.	Тур.	Max.	Units	Conditions	Ref.Fig.
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_{C} = 500 \mu A$	
$\Delta V_{(BR)CES} / \Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.40	—	V/°C	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1mA (25°C-150°C)	
V <sub>CE(on)</sub>	Collector-to-Emitter Voltage	—	1.95	2.35		$I_{C} = 30A, V_{GE} = 15V, T_{J} = 25^{\circ}C$	5,6,7
		—	2.40	2.75	V	I <sub>C</sub> = 30A, V <sub>GE</sub> = 15V, T <sub>J</sub> = 150°C	8,9,10
		—	2.6	2.95		$I_{C} = 30A, V_{GE} = 15V, T_{J} = 175^{\circ}C$	
V <sub>GE(th)</sub>	Gate Threshold Voltage	3.5	4.5	5.5	V	$V_{CE} = V_{GE}, I_C = 250 \mu A$	8,9,10
$\Delta V_{GE(th)} / \Delta T_J$	Threshold Voltage temp. coefficient	—	-10	_	mV/°C	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 1.0mA (25°C-150°C)	11
gfe	Forward Transconductance	—	18	—	S	V <sub>CE</sub> = 50V, I <sub>C</sub> = 50A, PW = 80µs	
I <sub>CES</sub>	Zero Gate Voltage Collector Current	—	5.0	250		$V_{GE} = 0V, V_{CE} = 600V$	
		—	1000	2000	μA	$V_{GE} = 0V, V_{CE} = 600V, T_{J} = 150^{\circ}C$	
		_	1830	3000		$V_{GE} = 0V, V_{CE} = 600V, T_{J} = 175^{\circ}C$	
I <sub>GES</sub>	Gate-to-Emitter Leakage Current	—	_	±100	nA	$V_{GE} = \pm 20V, V_{CE} = 0V$	

### Static or Switching Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions	Ref.Fig.
Q <sub>g</sub>	Total Gate Charge (turn-on)	_	102	153		I <sub>C</sub> = 30A	17
Q <sub>ge</sub>	Gate-to-Emitter Charge (turn-on)	—	14	21	nC	$V_{CC} = 400V$	CT1
Q <sub>gc</sub>	Gate-to-Collector Charge (turn-on)	_	44	66	1	V <sub>GE</sub> = 15V	
Eon	Turn-On Switching Loss	—	350	620		I <sub>C</sub> = 30A, V <sub>CC</sub> = 400V	CT4
E <sub>off</sub>	Turn-Off Switching Loss	_	825	955	μJ	$V_{GE} = 15V, R_{G} = 10\Omega, L = 200\mu H$	
E <sub>tot</sub>	Total Switching Loss	_	1175	1575	Ī	T <sub>J</sub> = 25°C ③	
t <sub>d(on)</sub>	Turn-On delay time	—	46	60		I <sub>C</sub> = 30A, V <sub>CC</sub> = 400V	
t,	Rise time	—	28	39	ns	$V_{GE} = 15V, R_{G} = 10\Omega, L = 200\mu H$	CT4
t <sub>d(off)</sub>	Turn-Off delay time	_	185	200	1	$T_{\rm J} = 25^{\circ}C$	
t <sub>f</sub>	Fall time	_	31	40	1		
E <sub>on</sub>	Turn-On Switching Loss	_	635	1085		I <sub>C</sub> = 30A, V <sub>CC</sub> = 400V	CT4
E <sub>off</sub>	Turn-Off Switching Loss	_	1150	1350	μJ	V <sub>GE</sub> = 15V, R <sub>G</sub> = 10Ω, L = 200μH	12,14
E <sub>tot</sub>	Total Switching Loss	_	1785	2435	1	T <sub>J</sub> = 150°C ③	WF1,WF2
t <sub>d(on)</sub>	Turn-On delay time	—	46	60		I <sub>C</sub> = 30A, V <sub>CC</sub> = 400V	13,15
t <sub>r</sub>	Rise time	_	28	39	ns	$V_{GE} = 15V, R_{G} = 10\Omega, L = 200\mu H$	CT4
t <sub>d(off)</sub>	Turn-Off delay time	—	205	235	1	T <sub>J</sub> = 150°C	WF1
t <sub>f</sub>	Fall time	—	32	42	1		WF2
L <sub>E</sub>	Internal Emitter Inductance	_	7.5	—	nH	Measured 5mm from package	
C <sub>ies</sub>	Input Capacitance	—	1750	—		$V_{GE} = 0V$	
C <sub>oes</sub>	Output Capacitance	_	160	—	pF	$V_{CC} = 30V$	16
C <sub>res</sub>	Reverse Transfer Capacitance	_	60	_	1	f = 1.0MHz	
RBSOA	Reverse Bias Safe Operating Area	FUL	L SQU	ARE		T <sub>J</sub> = 150°C, I <sub>C</sub> = 120A, Vp = 600V	4
						$V_{CC}$ =500V, $V_{GE}$ = +15V to 0V, $R_{G}$ =10 $\Omega$	CT2
SCSOA	Short Circuit Safe Operating Area	10	—	_	μs	$T_{\rm J} = 150^{\circ}$ C, Vp = 600V, $R_{\rm G} = 10\Omega$	CT3
						$V_{CC}=360V, V_{GE} = +15V$ to 0V	WF3
I <sub>SC</sub> (Peak)	Peak Short Circuit Collector Current	—	200	—	Α		WF3

Notes:

0  $V_{CC}$  = 80% (V\_{CES}),  $V_{GE}$  = 20V, L = 28  $\mu$ H, R\_G = 22  $\Omega$ .

O This is applied to D²Pak, when mounted on 1" square PCB ( FR-4 or G-10 Material ).

For recommended footprint and soldering techniques refer to application note #AN-994.

 $\ensuremath{\textcircled{}}$  Energy losses include "tail" and diode reverse recovery.

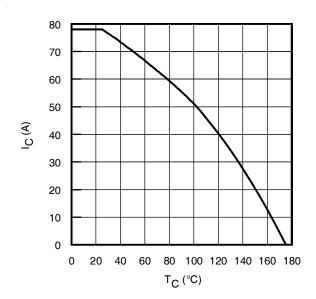
### **Qualification Information<sup>†</sup>**

		Automotive			
		(per AEC-Q101) <sup>††</sup>			
Qualification Level		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.			
		D <sup>2</sup> PAK	MSL1 <sup>†††</sup>		
Moisture Sen	Moisture Sensitivity Level		(per IPC/JEDEC J-STD-020)		
		TO-262	N/A		
	Machine Model	Class M4 (400V)			
		AEC-Q101-002			
	Human Body Model	Class H2 (4000V)			
ESD	ESD		AEC-Q101-001		
	Charged Device Model		Class C4 (1000V)		
		AEC-Q101-005			
RoHS Compl	iant	Yes			

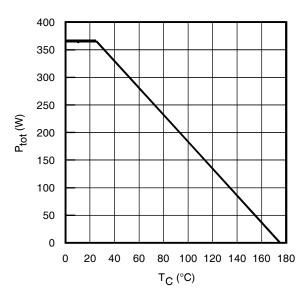
† Qualification standards can be found at International Rectifier's web site: http://www.irf.com

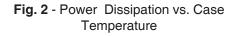
t+ Exceptions to AEC-Q101 requirements are noted in the qualification report.

111 Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information.









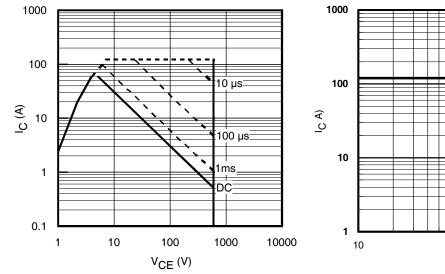
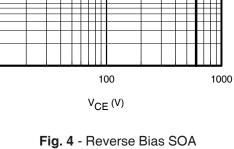
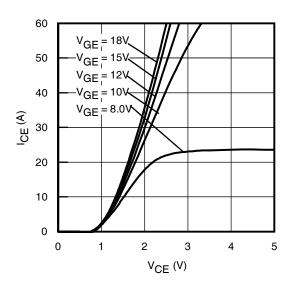


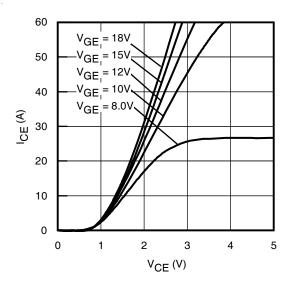
Fig. 3 - Forward SOA  $T_C = 25^{\circ}C$ ;  $T_J \le 150^{\circ}C$ 



 $T_{\rm J} = 150^{\circ}\text{C}; V_{\rm GE} = 15\text{V}$ 

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# Fig. 5 - Typ. IGBT Output Characteristics $T_J = -40^\circ C; \, tp = 80 \mu s$

Fig. 6 - Typ. IGBT Output Characteristics  $T_J$  = 25°C; tp = 80µs

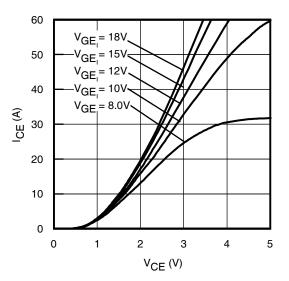
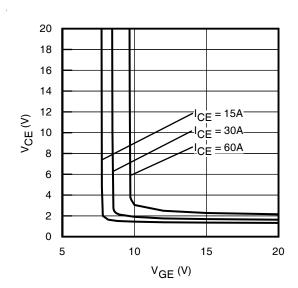
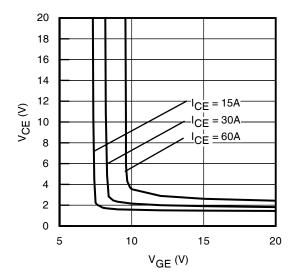
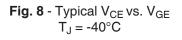
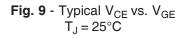


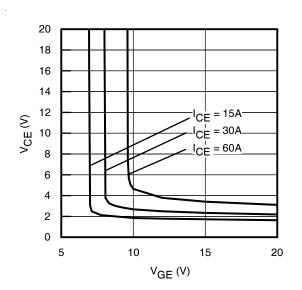
Fig. 7 - Typ. IGBT Output Characteristics  $T_J = 150^{\circ}C$ ; tp = 80 $\mu$ s

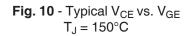


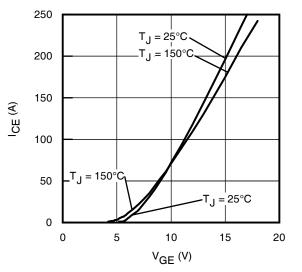


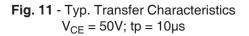




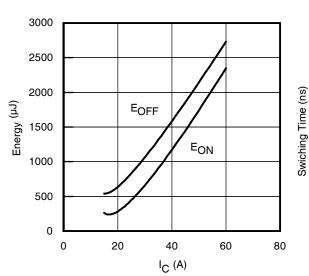


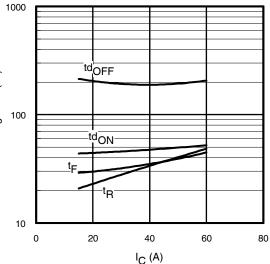


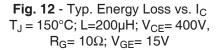


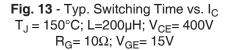


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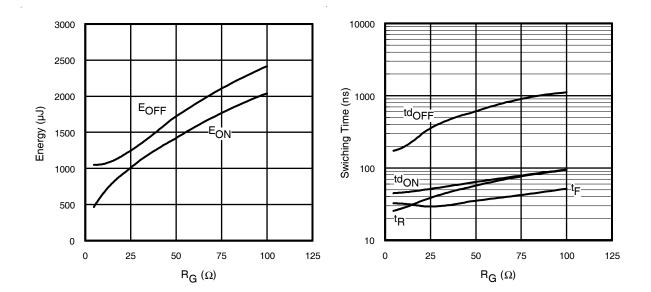
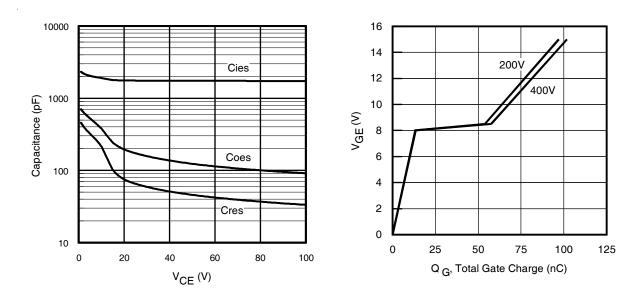
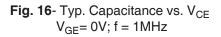
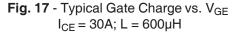


Fig. 14 - Typ. Energy Loss vs.  $R_G$ T<sub>J</sub> = 150°C; L=200µH; V<sub>CE</sub>= 400V I<sub>CE</sub>= 30A; V<sub>GE</sub>= 15V Fig. 15 - Typ. Switching Time vs.  $R_G$ T<sub>J</sub> = 150°C; L=200µH; V<sub>CE</sub>= 400V I<sub>CE</sub>= 30A; V<sub>GE</sub>= 15V







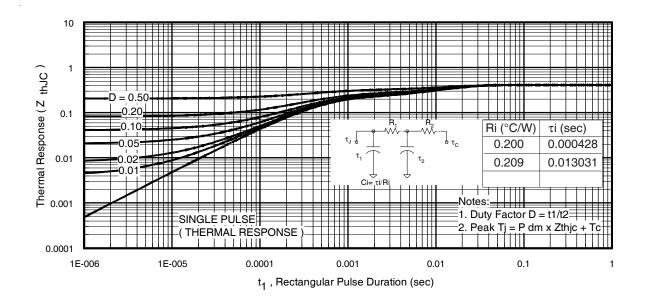
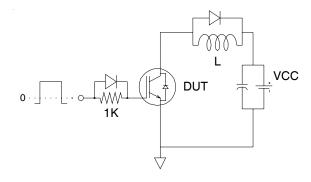


Fig 18. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)



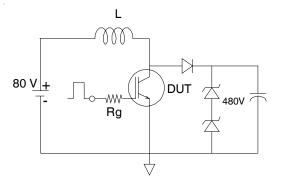


Fig.C.T.1 - Gate Charge Circuit (turn-off)



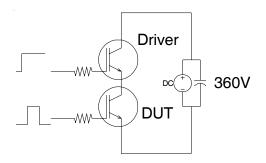


Fig.C.T.3 - S.C.SOA Circuit

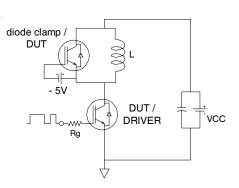


Fig.C.T.4 - Switching Loss Circuit

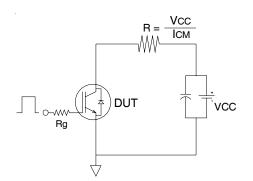
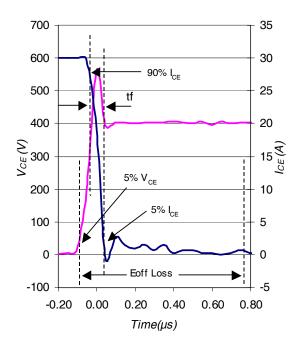
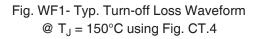
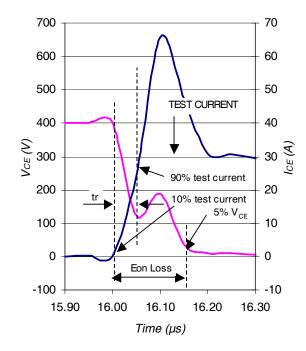
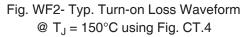


Fig.C.T.5 - Resistive Load Circuit









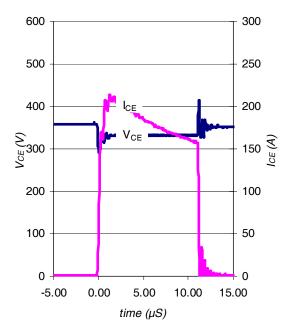
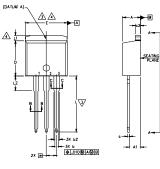


Fig. WF3- Typ. S.C Waveform @  $T_C = 150^{\circ}C$  using Fig. CT.3

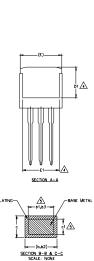
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Dimensions are shown in millimeters (inches)







N N N S		N				
В	MILLIM	ETERS	INC	HES	0 T E S	
D L	MIN.	MAX.	MIN.	MAX.	E S	
Α	4.06	4.83	.160	.190		
A1	2.03	3.02	.080	.119		
b	0.51	0.99	.020	.039		
ь1	0.51	0.89	.020	.035	5	
b2	1,14	1,78	.045	.070		
b3	1,14	1,73	.045	.068	5	
с	0.38	0.74	.015	.029		
c1	0.38	0.58	.015	.023	5	
c2	1,14	1.65	.045	.065		
D	8,38	9,65	.330	.380	3	
D1	6.86	-	.270	-	4	
Е	9.65	10.67	.380	.420	3,4	
E1	6.22	-	.245		4	
e	2.54	BSC	.100	BSC		
L	13.46	14.10	.530	.555		
L1	-	1.65	-	.065	4	
L2	3.56	3,71	,140	.146		

1. DIMENSIONING AND TOLERANCING PER ASME Y14,5M-1994 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

5. DIMENSION 61 AND c1 APPLY TO BASE METAL ONLY.

EXTREMES OF THE PLASTIC BODY.

6. CONTROLLING DIMENSION: INCH.

7.- OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

4 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.

NOTES

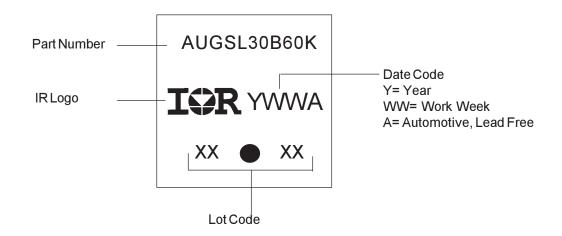
### LEAD ASSIGNMENTS

HEXFET 1.- GATE 2.- DRAIN 3.- SOURCE 4.- DRAIN

IGBTS, COPACK

1.- GATE 2.- COLLECTOR 3.- EMITTER 4.- COLLECTOR

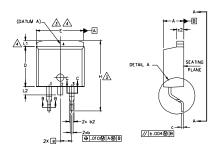
### TO-262 Part Marking Information



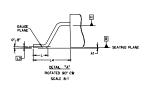
### Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

### D<sup>2</sup>Pak (TO-263AB) Package Outline

Dimensions are shown in millimeters (inches)

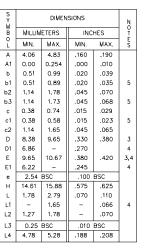






A

MEW A-A



1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994

3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH, MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.

4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, LI, DI & EI.

2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

5. DIMENSION 61 AND c1 APPLY TO BASE METAL ONLY. 6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.

8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

7. CONTROLLING DIMENSION: INCH.

NOTES

LEAD ASSIGNMENTS

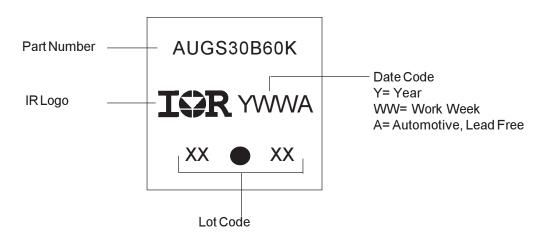
HEXFET 1.- GATE 2, 4.- DRAIN 3.- SOURCE

IGBTS, COPACK 1.- GATE 2, 4.- COLLECTOR 3.- EMITTER

DIODES 1.– ANODE \* 4.– CATHODE 3.– ANODE 2.

\* PART DEPENDENT.

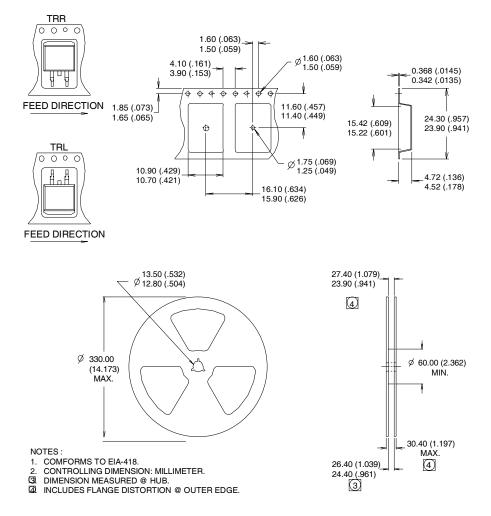
D<sup>2</sup>Pak (TO-263AB) Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

### D<sup>2</sup>Pak (TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



### Ordering Information

Base part number	Package Type	Standard Pack	Complete Part Number	
		Form	Quantity	
AUIRGSL30B60K	TO-262	Tube	50	AUIRGSL30B60K
AUIRGS30B60K	D2Pak	Tube	50	AUIRGS30B60K
		Tape and Reel Left	800	AUIRGS30B60KTRL
		Tape and Reel Right	800	AUIRGS30B60KTRR

### **IMPORTANT NOTICE**

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